

IN THE CLAIMS:

1-17. (Canceled)

18. (Currently Amended) An organic electroluminescence display device comprising:

a resin substrate;

an insulating film comprising a nitride on the resin substrate; and

a thin film transistor formed over the insulating film[[]; and]] , said thin film transistor comprising:

a crystalline semiconductor layer formed over the insulating film and including at least a channel region, source and drain regions and a pair of lightly doped regions between the channel region and said source and drain regions;

a gate insulator formed on the crystalline semiconductor layer; and

a gate electrode formed over the channel region with the gate insulator interposed therebetween wherein boundaries between said channel region and said pair of lightly doped regions are aligned with side edges of the gate electrode,

an interlayer insulating film comprising an organic resin over the thin film transistor;

and

an electroluminescent element electrically connected to said thin film transistor, said electroluminescent element having a light emitting layer comprising an organic material.

19. (Previously Presented) The organic electroluminescence display device according to claim 18 wherein said resin substrate comprises polyethylene terephthalate.

20. (Previously Presented) The organic electroluminescence display device according to claim 18 wherein said insulating film comprises a material selected from the group consisting of silicon nitride and silicon oxy-nitride.

21. (Currently Amended) An organic electroluminescence display device comprising:

- a resin substrate;
- an underlying insulating film formed on the resin substrate; and
- a thin film transistor formed over the underlying insulating film[, and]], said thin film transistor comprising:
 - a crystalline semiconductor layer formed over the insulating film and including at least a channel region, source and drain regions and a pair of lightly doped regions between the channel region and said source and drain regions;
 - a gate insulator formed on the crystalline semiconductor layer; and
 - a gate electrode formed over the channel region with the gate insulator interposed therebetween wherein boundaries between said channel region and said pair of lightly doped regions are aligned with side edges of the gate electrode,
 - an interlayer insulating film comprising an organic resin over the thin film transistor; and
 - an electroluminescent element electrically connected to said thin film transistor, said electroluminescent element having a light emitting layer comprising an organic material,
 - wherein the underlying insulating film comprises a first insulating film comprising a nitride and a second insulating film comprising silicon oxide.

22. (Previously Presented) The organic electroluminescence display device according to claim 22 wherein said resin substrate comprises polyethylene terephthalate.

23. (Previously Presented) The organic electroluminescence display device according to claim 22 wherein said first insulating film comprises a material selected from the group consisting of silicon nitride and silicon oxy-nitride.

24-43. (Canceled)

44. (New) An organic electroluminescence display device comprising:

- a resin substrate;
- an insulating film comprising a nitride on the resin substrate; and
- a first thin film transistor formed over the insulating film;
- an electroluminescent element electrically connected to said thin film transistor, said electroluminescent element having a light emitting layer comprising an organic material;
- a driver circuit comprising at least one second thin film transistor; and
- an interlayer insulating film comprising an organic resin over the first thin film transistor and the driver circuit,

each of said first and second thin film transistors comprising:

- a crystalline semiconductor layer formed over the insulating film and including at least a channel region, source and drain regions and a pair of lightly doped regions between the channel region and said source and drain regions;
- a gate insulator formed on the crystalline semiconductor layer; and

a gate electrode formed over the channel region with the gate insulator interposed therebetween wherein boundaries between said channel region and said pair of lightly doped regions are aligned with side edges of the gate electrode.

45. (New) The organic electroluminescence display device according to claim 44 wherein said resin substrate comprises polyethylene terephthalate.

46. (New) The organic electroluminescence display device according to claim 44 wherein said insulating film comprises a material selected from the group consisting of silicon nitride and silicon oxy-nitride.

47. (New) An organic electroluminescence display device comprising:

a resin substrate;

an insulating film comprising a nitride on the resin substrate, said underlying insulating film comprising a first insulating film comprising a nitride and a second insulating film comprising silicon oxide;

a first thin film transistor formed over the insulating film;

an electroluminescent element electrically connected to said thin film transistor, said electroluminescent element having a light emitting layer comprising an organic material; and

a driver circuit comprising at least one second thin film transistor;

an interlayer insulating film comprising an organic resin over the first thin film transistor and the driver circuit,

each of said first and second thin film transistors comprising:

a crystalline semiconductor layer formed over the insulating film and including at least a channel region, source and drain regions and a pair of lightly doped regions between the channel region and said source and drain regions;

a gate insulator formed on the crystalline semiconductor layer; and

a gate electrode formed over the channel region with the gate insulator interposed therebetween wherein boundaries between said channel region and said pair of lightly doped regions are aligned with side edges of the gate electrode.

48. (New) The organic electroluminescence display device according to claim 47 wherein said resin substrate comprises polyethylene terephthalate.

49. (New) The organic electroluminescence display device according to claim 47 wherein said insulating film comprises a material selected from the group consisting of silicon nitride and silicon oxy-nitride.